VS-50RIA Series

Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 50 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)}	50 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V _{TM}	1.60 V			
I _{GT}	100 mA			
TJ	-40 °C to 125 °C			
Package	TO-65 (TO-208AC)			
Circuit configuration	Single SCR			

FEATURES

- High current rating
- Excellent dynamic characteristics
- dV/dt = 1000 V/µs option
- Superior surge capabilities
- Standard package
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Phase control applications in converters
- Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		50	A		
I _{T(AV)}	T _C	94	°C		
I _{T(RMS)}		80	A		
I _{TSM}	50 Hz	1430			
	60 Hz	1490	— A		
l ² t	50 Hz	10.18	kA ² s		
1-1	60 Hz	9.30	KA-S		
V _{DRM} /V _{RRM}		100 to 1200	V		
tq	Typical	110	μs		
TJ		-40 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$				
	10	100	150					
	20	200	300					
	40	400	500					
VS-50RIA	60	600	700	15				
	80	800	900					
	100	1000	1100					
	120	1200	1300					

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs ⁽²⁾ For voltage pulses with $t_p \le 5$ ms

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ABSOLUTE MAXIMUM RATI	NGS					
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current		190º oipuoo	180° sinusoidal conduction		50	А
at case temperature	I _{T(AV)}	Too Sinusoi			94	°C
Maximum RMS on-state current	I _{T(RMS)}				80	А
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1490	_
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{BBM}		1200	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
Maximum I ² t for fusing		t = 10 ms		initial $T_J = T_J$ maximum	10.18	kA ² s
	l ² t	t = 8.3 ms			9.30	
	1-1	t = 10 ms	100 % V _{RRM} reapplied		7.20	
		t = 8.3 ms			6.56	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum		101.8	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.94	v	
High level value of threshold voltage	V _{T(TO)2}	(π x I _{T(AV)} < I	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum		4.08	mΩ	
High level value of on-state slope resistance	r _{t2}	($\pi \ge I_{T(AV)} < I < 20 \ge \pi \ge I_{T(AV)}$), $T_J = T_J$ maximum			3.34	11152
Maximum on-state voltage	V _{TM}	I _{pk} = 157 A, T _J = 25 °C			1.60	V
Maximum holding current	Iн	$T_J = 25 \text{ °C}, a$ initial $I_T = 2 a$	anode supply 22 ' A	V, resistive load,	200	mA
Latching current	١ _L	Anode supp	ly 6 V, resistive lo	ad	400	

SWITCHING						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of	$V_{DRM} \leq 600 \ V$	dl/dt	$T_C = 125$ °C, $V_{DM} = Rated V_{DRM}$, dl/dt Gate pulse = 20 V, 15 Ω, $t_p = 6 \mu s$, $t_r = 0.1 \mu s$ maximum		A/us	
rise of turned-on current	$V_{DRM} \le 1600 \text{ V}$		$I_{TM} = (2 \text{ x rated dl/dt}) \text{ A}$	100	Ανμs	
Typical delay time		t _d	$T_{C} = 25 \text{ °C}, V_{DM} = \text{Rated } V_{DRM}, I_{TM} = 10 \text{ A dc resistive circuit}$ Gate pulse = 10 V, 15 Ω source, $t_{p} = 20 \mu\text{s}$			
Typical turn-off time		tq	$T_{C} = 125 \text{ °C}, I_{TM} = 50 \text{ A}, \text{ reapplied } dV/dt = 20 \text{ V/}\mu\text{s}$ dIr/dt = - 10 A/ μ s, V _R = 50 V		μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	200	V/µs	
off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	500 ⁽¹⁾	v/µs	

Note

 $^{(1)}$ Available with dV/dt = 1000 V/µs, to complete code add S90 i.e. 50RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \leq \xi$	5 ms	10	w
Maximum average gate power	P _{G(AV)}			2.5	- vv
Maximum peak positive gate current	I _{GM}			2.5	А
Maximum peak positive gate voltage	+V _{GM}			20	v
Maximum peak negative gate voltage	-V _{GM}			10	V
	I _{GT}	T _J = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	250	mA
DC gate current required to trigger		T _J = 25 °C		100	
		T _J = 125 °C		50	
		T _J = - 40 °C		3.5	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	V
DC gate current not to trigger	I _{GD}	$T_J = T_J maximum,$ $V_{DRM} = Rated voltage$	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	v

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.35	— к/w	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25		
		Non-lubricated threads	3.4 ^{+ 0 - 10 %} (30)	N⋅m	
Allowable mounting torque		Lubricated threads	2.3 ^{+ 0 - 10} % (20)	(lbf ∙ in	
Approvimate weight			28	g	
Approximate weight			1.0	oz.	
Case style		See dimensions - link at the end of datasheet	TO-65 (TO-	TO-65 (TO-208AC)	

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J maximum$	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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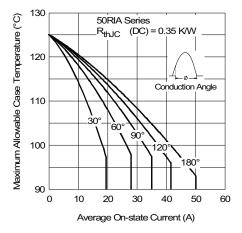


Fig. 1 - Current Ratings Characteristics

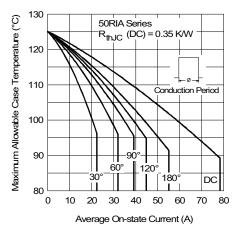


Fig. 2 - Current Ratings Characteristics

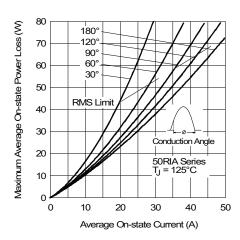


Fig. 3 - On-State Power Loss Characteristics

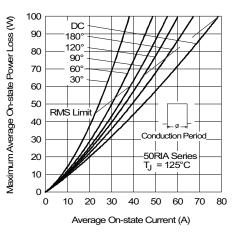


Fig. 4 - On-State Power Loss Characteristics

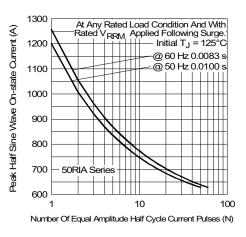


Fig. 5 - Maximum Non-Repetitive Surge Current

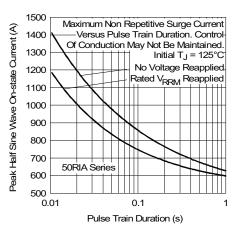


Fig. 6 - Maximum Non-Repetitive Surge Current

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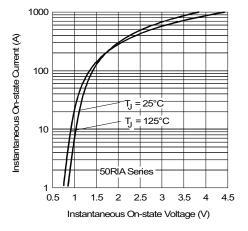
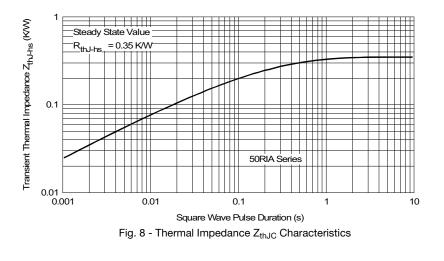


Fig. 7 - Forward Voltage Drop Characteristics



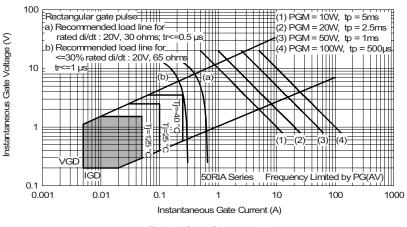
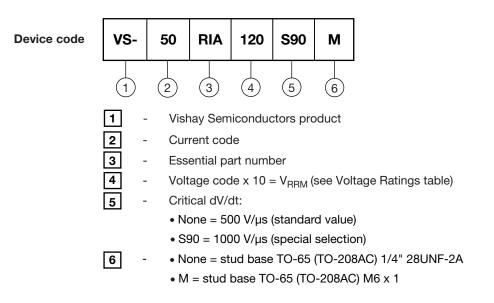


Fig. 9 - Gate Characteristics

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ORDERING INFORMATION TABLE

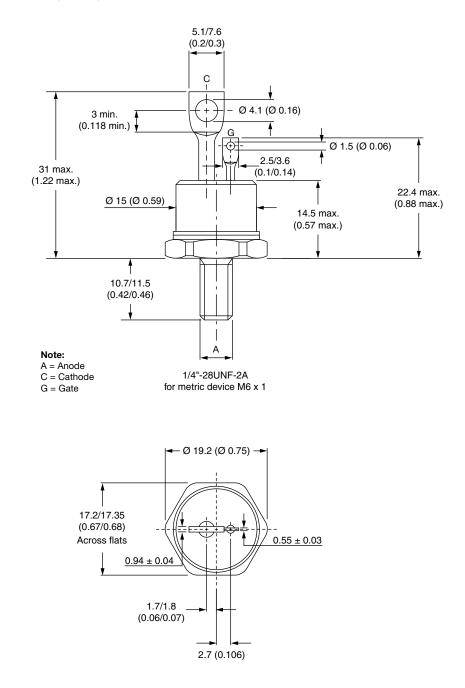


LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95334			



TO-208AC (TO-65)

DIMENSIONS in millimeters (inches)





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